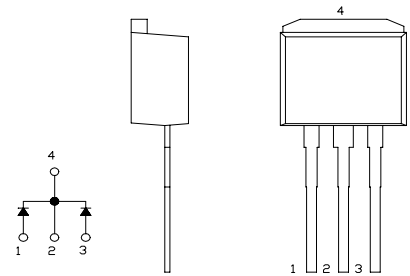


SBD Type : C10T10Q-11A

OUTLINE DRAWING

FEATURES

- *Tabless TO-220
- *Dual Diodes – Cathode Common
- *Low Forward Voltage Drop
- *High Surge Capability
- *Tj=150 °C operation



Maximum Ratings

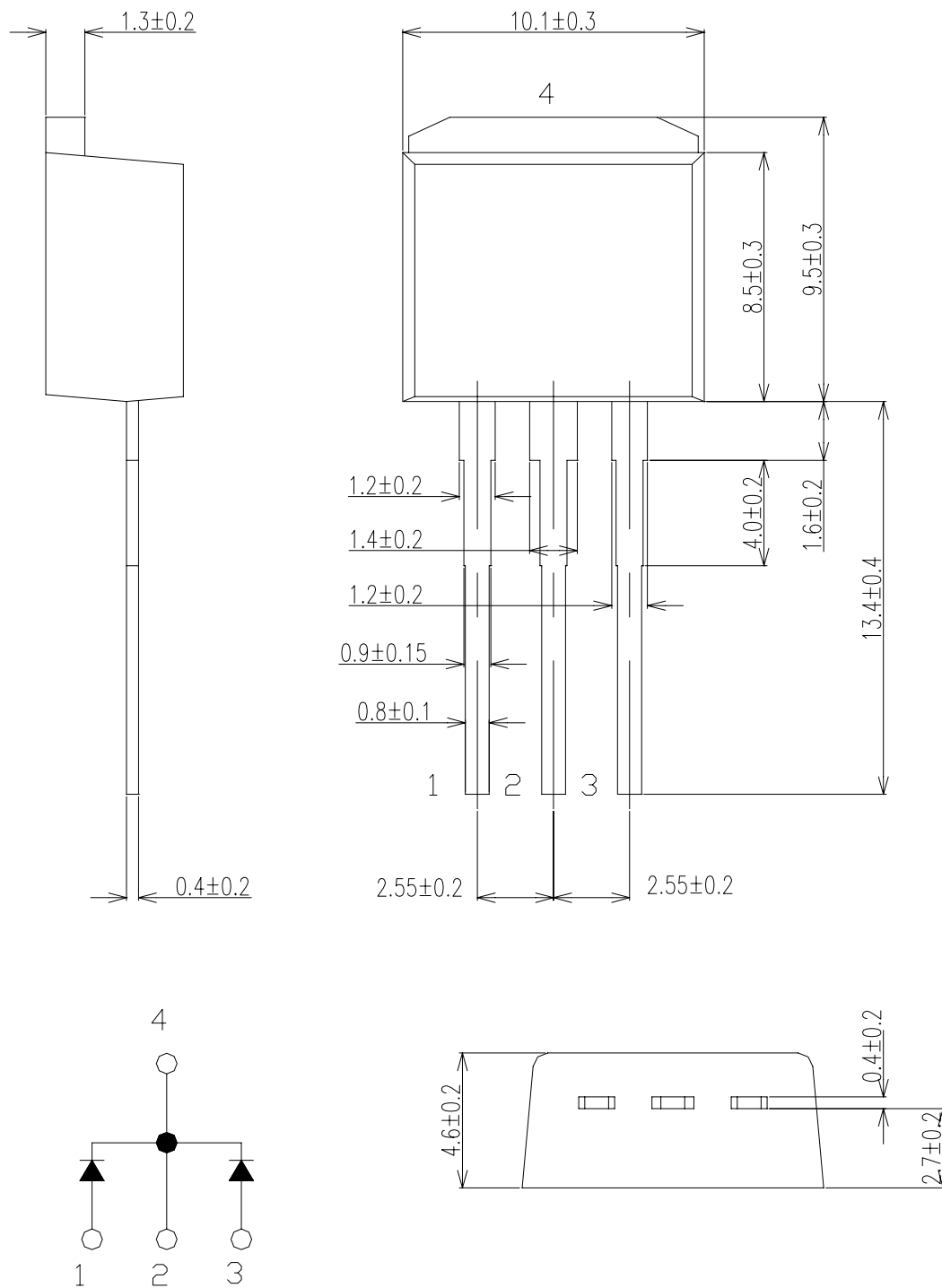
Approx Net Weight: 1.45g

Rating	Symbol	C10T10Q-11A			Unit
Repetitive Peak Reverse Voltage	V _{RRM}	100			V
Average Rectified Output Current	I _O	10	Tc=121°C	50 Hz Full Sine Wave Resistive Load	A
RMS Forward Current	I _{F(RMS)}	11.1			A
Surge Forward Current	I _{FSM}	120	50Hz Full Sine Wave ,1cycle Non-repetitive		A
Operating JunctionTemperature Range	T _{jw}	-40 to +150			°C
Storage Temperature Range	T _{stg}	-40 to +150			°C

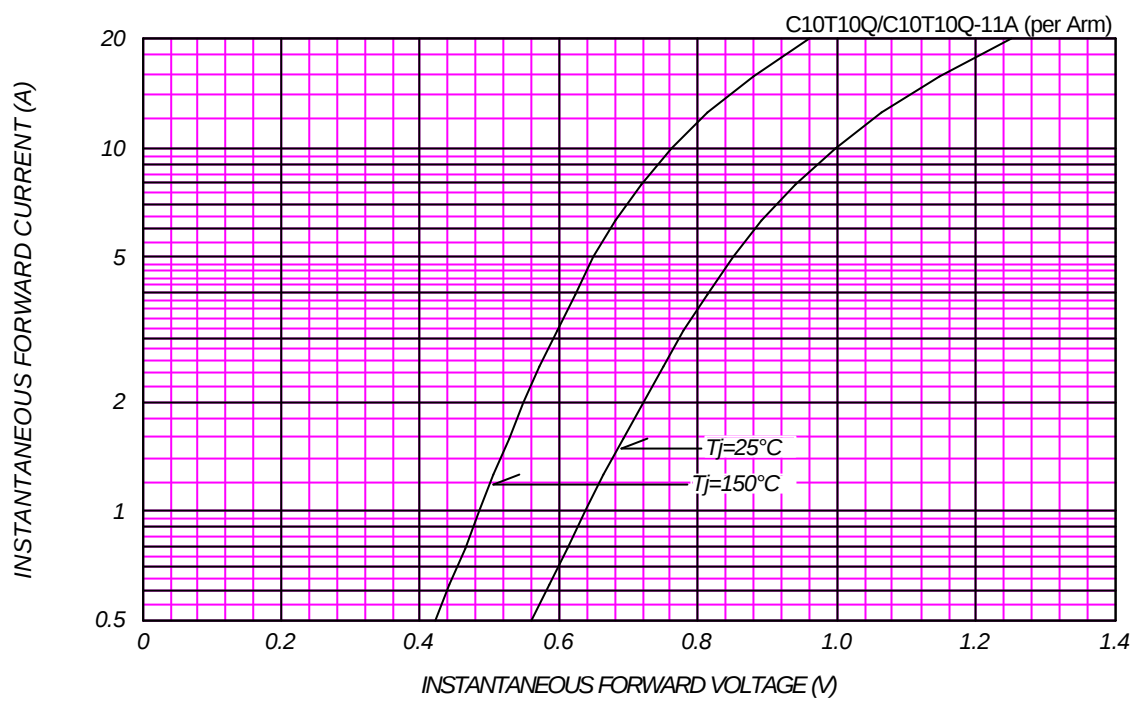
Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	I_{RM}	$T_j= 25^{\circ}C, V_{RM}= V_{RRM}$ per arm	-	-	1	mA
Peak Forward Voltage	V_{FM}	$T_j= 25^{\circ}C, I_{FM}= 5 A$ per arm	-	-	0.85	V
Thermal Resistance	$R_{th(j-c)}$	Junction to Case	-	-	3	°C /W

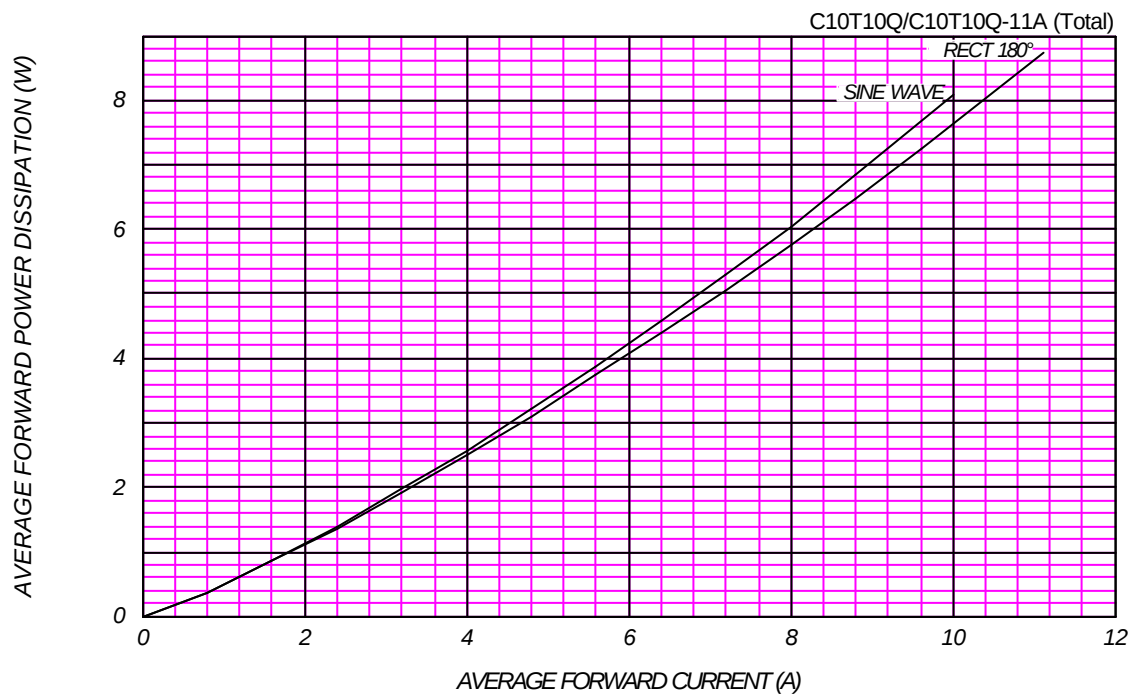
C_T_ 11A OUTLINE DRAWING (Dimensions in mm)



FORWARD CURRENT VS. VOLTAGE



AVERAGE FORWARD POWER DISSIPATION



PEAK REVERSE CURRENT VS. PEAK REVERSE VOLTAGE

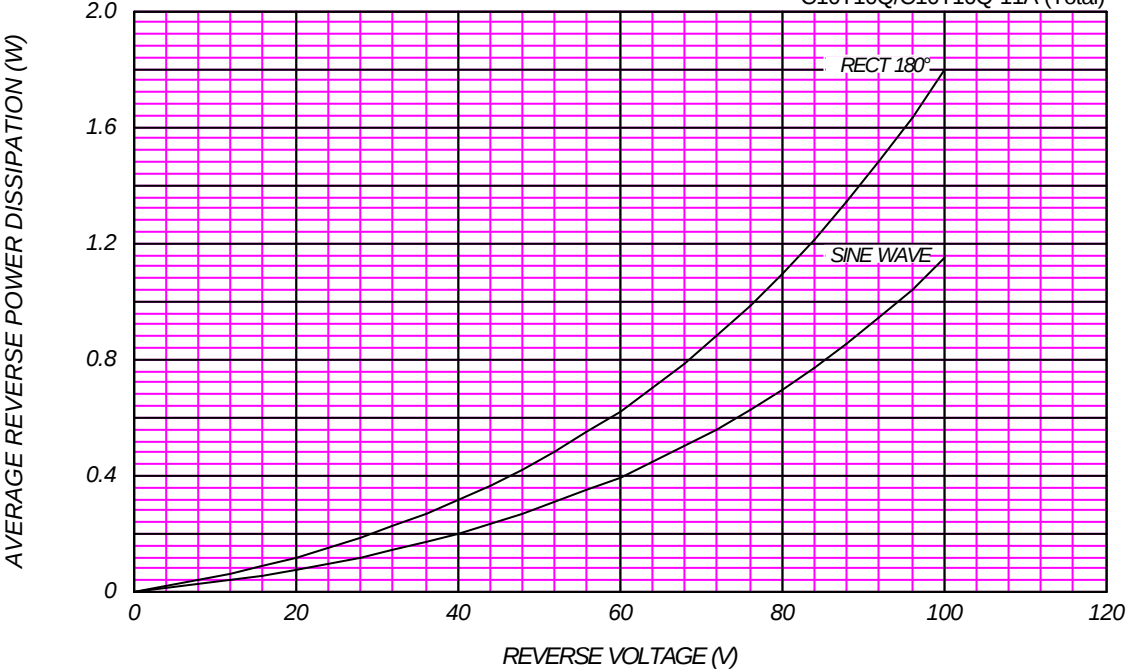
T_j= 150 °C

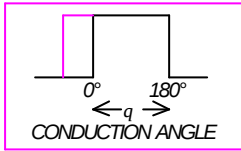
C10T10Q/C10T10Q-11A (per Arm)



AVERAGE REVERSE POWER DISSIPATION

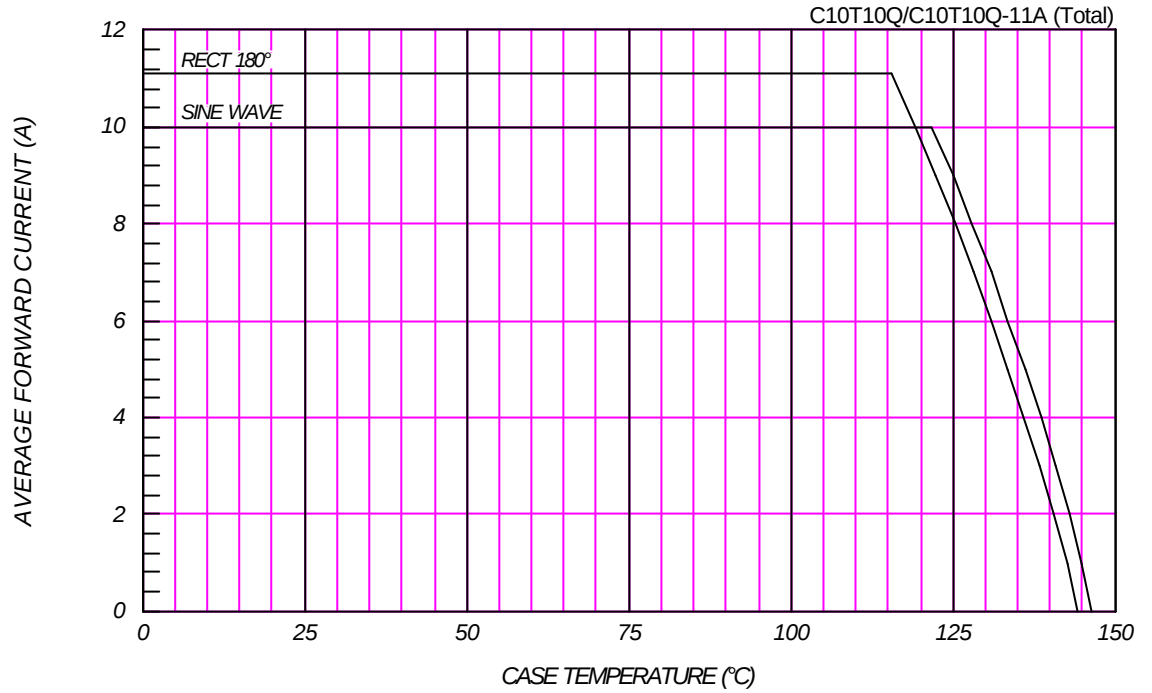
C10T10Q/C10T10Q-11A (Total)





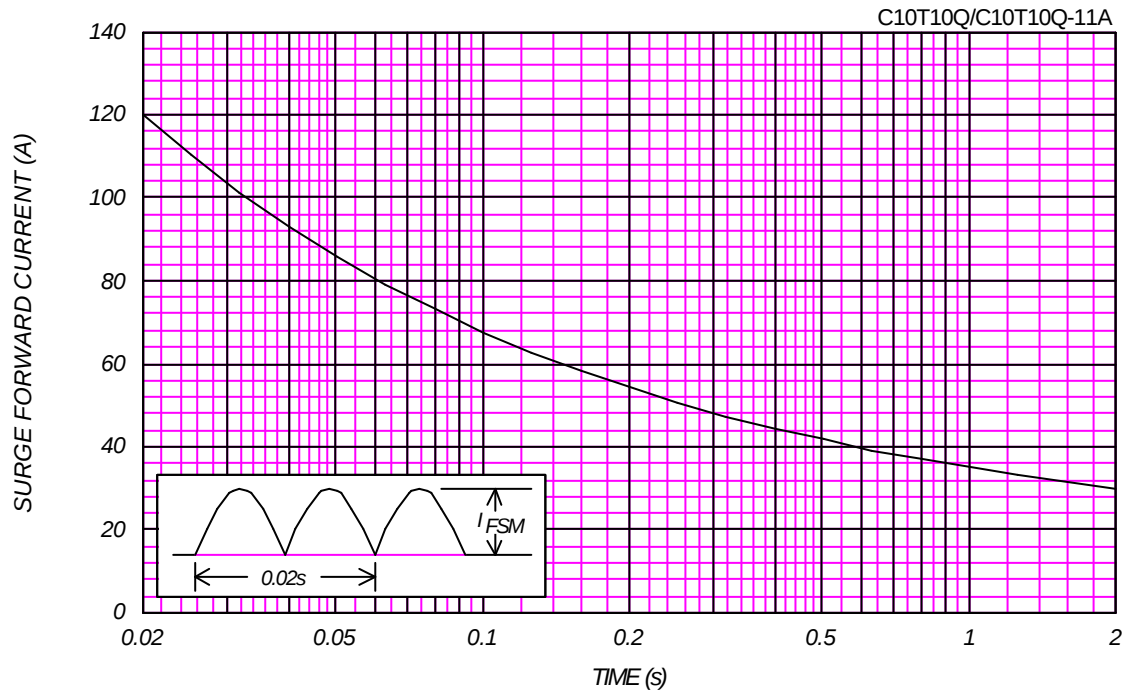
AVERAGE FORWARD CURRENT VS. CASE TEMPERATURE

$V_{RM} = 100V$



SURGE CURRENT RATINGS

$f = 50Hz$, Sine Wave, Non-Repetitive, No Load



JUNCTION CAPACITANCE VS. REVERSE VOLTAGE

$T_j=25^{\circ}\text{C}$, $V_m=20\text{mV}_{\text{RMS}}$, $f=100\text{kHz}$, Typical Value

C10T10Q/C10T10Q-11A (per Arm)

